# 8-Bit Serial-Input/Serial or Parallel-Output Shift Register with Latched 3-State Outputs and LSTTL Compatible Inputs

# **High-Performance Silicon-Gate CMOS**

The MC74HCT595A consists of an 8-bit shift register and an 8-bit D-type latch with three-state parallel outputs. The shift register accepts serial data and provides a serial output. The shift register also provides parallel data to the 8-bit latch. The shift register and latch have independent clock inputs. This device also has an asynchronous reset for the shift register.

The HCT595A directly interfaces with the SPI serial data port on CMOS MPUs and MCUs. The device inputs are compatible with standard CMOS or LSTTL outputs.

# **Features**

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 328 FETs or 82 Equivalent Gates
- Improvements over HC595 / HCT595
  - Improved Propagation Delays
  - 50% Lower Quiescent Power
  - Improved Input Noise and Latchup Immunity
- Pb-Free Packages are Available\*



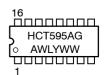
# ON Semiconductor®

http://onsemi.com

# MARKING DIAGRAMS

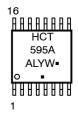


SOIC-16 D SUFFIX CASE 751B





TSSOP-16 DT SUFFIX CASE 948F



A = Assembly Location

WL, L = Wafer Lot YY, Y = Year WW, W = Work Week G, = Pb-Free Package

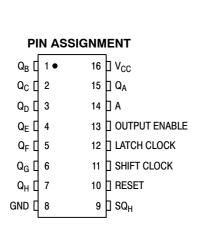
(Note: Microdot may be in either location)

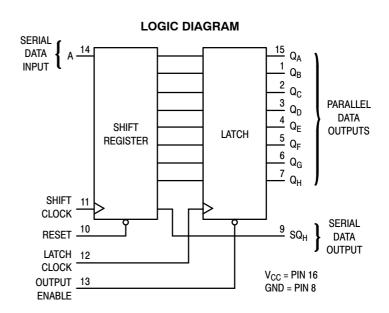
# **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.





# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74HCT595ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HCT595ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74HCT595ADTG	TSSOP-16*	96 Units / Rail
MC74HCT595ADTR2G	TSSOP-16* (Pb-Free)	2500 Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

# **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-$ 0.5 to $V_{CC}$ + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + $0.5$	V
l <sub>in</sub>	DC Input Current, per Pin	± 20	mA
l <sub>out</sub>	DC Output Current, per Pin	± 35	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	± 75	mA
P <sub>D</sub>	Power Dissipation in Still Air, SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V<sub>in</sub> and Vout should be constrained to the range GND  $\leq$  (V<sub>in</sub> or V<sub>out</sub>)  $\leq$  V<sub>CC</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device

SOIC Package: - 7 mW/°C from 65° to 125°C TSSOP Package: - 6.1 mW/°C from 65° to 125°C †Derating

# RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range, All Package Types	<b>– 55</b>	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Figure 1)	0	500	ns

# DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

			Vcc	Guaranteed Limit				
Symbol	Parameter	Test Conditions	V	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit	
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out}$ = 0.1 V or $V_{CC}$ – 0.1 V $ I_{out}  \le 20 \mu A$	4.5 to 5.5	2.0	2.0	2.0	V	
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	4.5 to 5.5	0.8	0.8	0.8	٧	
V <sub>OH</sub>	$\begin{array}{c} \mbox{Minimum High-Level Output} \\ \mbox{Voltage, } \mbox{Q}_{\mbox{A}} - \mbox{Q}_{\mbox{H}} \end{array}$	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu A$	4.5	4.4	4.4	4.4	V	
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad  I_{out}  \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7		
V <sub>OL</sub>	$\begin{array}{c} \text{Maximum Low-Level Output} \\ \text{Voltage, } Q_{\text{A}} - Q_{\text{H}} \end{array}$	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu A$	4.5	0.1	0.1	0.1	V	
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad  I_{out}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4		
V <sub>OH</sub>	Minimum High-Level Output Voltage, SQ <sub>H</sub>	$V_{in} = V_{IH} \text{ or } V_{IL}$ $II_{out}I \leq 20 \ \mu A$	4.5	4.4	4.4	4.4	V	
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad II_{out}I \leq 4.0 \text{ mA}$	4.5	3.98	3.84	3.7		
V <sub>OL</sub>	Maximum Low-Level Output Voltage, SQ <sub>H</sub>	$V_{in} = V_{IH} \text{ or } V_{IL}$ $II_{out}I \leq 20 \ \mu A$	4.5	0.1	0.1	0.1	V	
		$V_{in} = V_{IH} \text{ or } V_{IL} \qquad II_{out}I \leq 4.0 \text{ mA}$	4.5	0.26	0.33	0.4		
l <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	5.5	± 0.1	± 1.0	± 1.0	μΑ	
l <sub>OZ</sub>	Maximum Three–State Leakage Current, Q <sub>A</sub> – Q <sub>H</sub>	Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	5.5	± 0.5	± 5.0	± 10	μΑ	
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0	40	160	μΑ	
$\Delta I_{CC}$	Additional Quiescent Supply	V <sub>in</sub> = 2.4V, Any One Input V <sub>in</sub> = V <sub>CC</sub> or GND, Other Inputs		≥ <b>–55</b> °C	25 to	125°C		
	Ounent	$V_{in} = V_{CC}$ of GND, Other inputs $I_{out} = 0\mu A$	5.5	2.9	2	.4	mA	

# AC ELECTRICAL CHARACTERISTICS ( $C_L$ = 50 pF, Input $t_r$ = $t_f$ = 6.0 ns)

		V <sub>CC</sub>	Guar			
Symbol	Parameter	v	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 7)	4.5 to 5.5	30	24	20	MHz
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Shift Clock to SQ <sub>H</sub> (Figures 1 and 7)	4.5 to 5.5	28	35	42	ns
t <sub>PHL</sub>	Maximum Propagation Delay, Reset to SQ <sub>H</sub> (Figures 2 and 7)	4.5 to 5.5	29	36	44	ns
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Latch Clock to Q <sub>A</sub> – Q <sub>H</sub> (Figures 3 and 7)	4.5 to 5.5	28	35	42	ns
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Q <sub>A</sub> – Q <sub>H</sub> (Figures 4 and 8)	4.5 to 5.5	30	38	45	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Output Enable to Q <sub>A</sub> – Q <sub>H</sub> (Figures 4 and 8)	4.5 to 5.5	27	34	41	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Q <sub>A</sub> – Q <sub>H</sub> (Figures 3 and 7)	4.5 to 5.5	12	15	18	ns
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, SQ <sub>H</sub> (Figures 1 and 7)	4.5 to 5.5	15	19	22	ns
C <sub>in</sub>	Maximum Input Capacitance	_	10	10	10	pF
C <sub>out</sub>	Maximum Three-State Output Capacitance (Output in High-Impedance State), Q <sub>A</sub> - Q <sub>H</sub>	_	15	15	15	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
C <sub>PD</sub>	Power Dissipation Capacitance (Per Package)*	300	pF

<sup>\*</sup>Used to determine the no-load dynamic power consumption:  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ .

# **TIMING REQUIREMENTS** (Input $t_r = t_f = 6.0 \text{ ns}$ )

		V <sub>CC</sub>	Guara	t		
Symbol	Parameter	v	25°C to -55°C	≤ <b>85</b> °C	≤ 125°C	Unit
t <sub>su</sub>	Minimum Setup Time, Serial Data Input A to Shift Clock (Figure 5)	4.5 to 5.5	10	13	15	ns
t <sub>su</sub>	Minimum Setup Time, Shift Clock to Latch Clock (Figure 6)	4.5 to 5.5	15	19	22	ns
t <sub>h</sub>	Minimum Hold Time, Shift Clock to Serial Data Input A (Figure 5)	4.5 to 5.5	5.0	5.0	5.0	ns
t <sub>rec</sub>	Minimum Recovery Time, Reset Inactive to Shift Clock (Figure 2)		10	13	15	ns
t <sub>w</sub>	Minimum Pulse Width, Reset (Figure 2)		12	15	18	ns
t <sub>w</sub>	Minimum Pulse Width, Shift Clock (Figure 1)		10	13	15	ns
t <sub>w</sub>	Minimum Pulse Width, Latch Clock (Figure 6)		10	13	15	ns
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times (Figure 1)	4.5 to 5.5	500	500	500	ns

# **FUNCTION TABLE**

	Inputs							Resulting Function				
Operation	Reset	Serial Input A	Shift Clock	Latch Clock	Output Enable	Shift Register Contents	Latch Register Contents	Serial Output SQ <sub>H</sub>	Parallel Outputs Q <sub>A</sub> – Q <sub>H</sub>			
Reset shift register	L	Х	Х	L, H, ↓	L	L	U	L	U			
Shift data into shift register	Н	D	1	L, H, ↓	L	$\begin{array}{c} \text{D} \rightarrow \text{SR}_{A};\\ \text{SR}_{N} \rightarrow \text{SR}_{N+1} \end{array}$	U	$SR_G \rightarrow SR_H$	U			
Shift register remains unchanged	Н	Х	L, H, ↓	L, H, ↓	L	U	U	U	U			
Transfer shift register contents to latch register	Н	Х	L, H, ↓	1	L	U	$SR_N \rightarrow LR_N$	U	SR <sub>N</sub>			
Latch register remains unchanged	Х	Х	Х	L, H, ↓	L	*	U	*	U			
Enable parallel outputs	Х	Х	Х	Х	L	*	**	*	Enabled			
Force outputs into high impedance state	Х	Х	Х	Х	Н	*	**	*	Z			

SR = shift register contents

D = data (L, H) logic level

↑ = Low-to-High

\* = depends on Reset and Shift Clock inputs

LR = latch register contents

U = remains unchanged

 $\downarrow$  = High-to-Low

\*\* = depends on Latch Clock input

# **PIN DESCRIPTIONS**

# INPUTS A (Pin 14)

Serial Data Input. The data on this pin is shifted into the 8-bit serial shift register.

# **CONTROL INPUTS**Shift Clock (Pin 11)

Shift Register Clock Input. A low-to-high transition on this input causes the data at the Serial Input pin to be shifted into the 8-bit shift register.

# Reset (Pin 10)

Active-low, Asynchronous, Shift Register Reset Input. A low on this pin resets the shift register portion of this device only. The 8-bit latch is not affected.

# Latch Clock (Pin 12)

Storage Latch Clock Input. A low-to-high transition on this input latches the shift register data.

# **Output Enable (Pin 13)**

Active–low Output Enable. A low on this input allows the data from the latches to be presented at the outputs. A high on this input forces the outputs  $(Q_A-Q_H)$  into the high–impedance state. The serial output is not affected by this control unit.

# **OUTPUTS**

Q<sub>A</sub> - Q<sub>H</sub> (Pins 15, 1, 2, 3, 4, 5, 6, 7)

Noninverted, 3-state, latch outputs.

# SQ<sub>H</sub> (Pin 9)

Noninverted, Serial Data Output. This is the output of the eighth stage of the 8-bit shift register. This output does not have three-state capability.

# **SWITCHING WAVEFORMS**

 $(V_1 = 0 \text{ to } 3 \text{ V}, V_M = 1.3 \text{ V})$ 

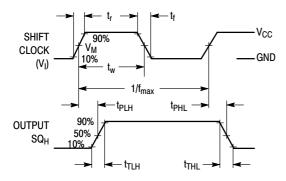


Figure 1.

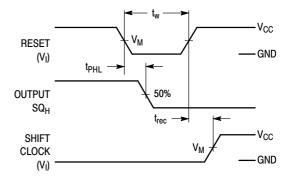


Figure 2.

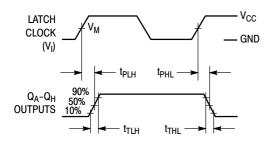


Figure 3.

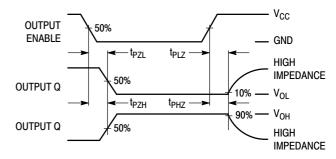
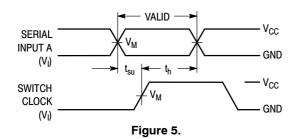
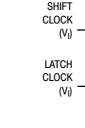


Figure 4.





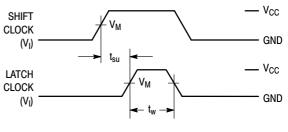
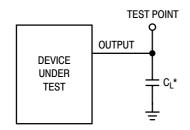


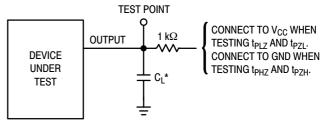
Figure 6.

# **TEST CIRCUITS**



\*Includes all probe and jig capacitance

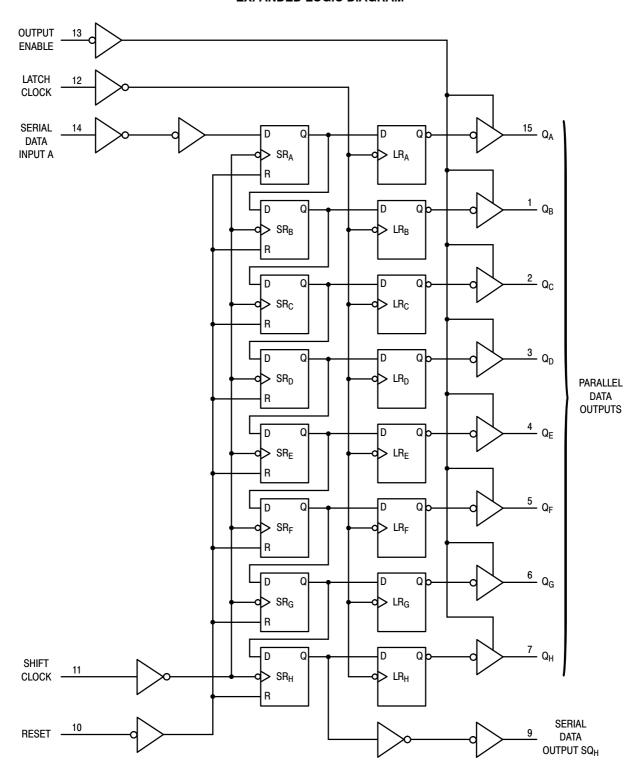
Figure 7.



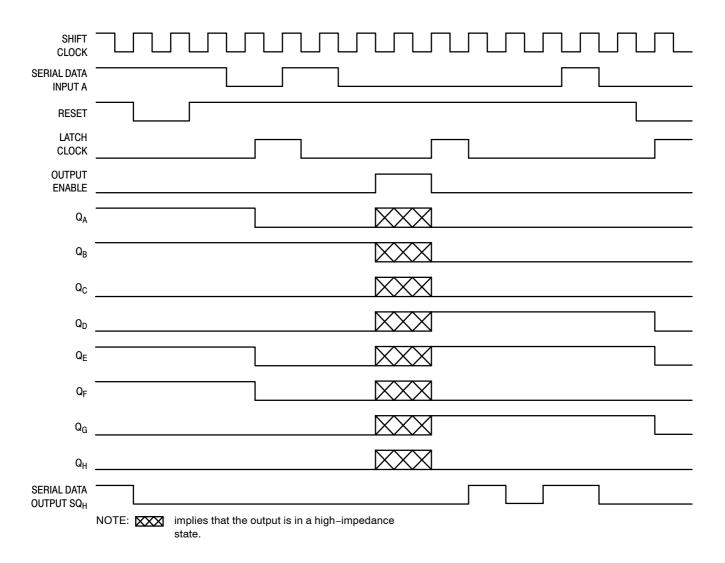
\*Includes all probe and jig capacitance

Figure 8.

# **EXPANDED LOGIC DIAGRAM**



# **TIMING DIAGRAM**



# **MECHANICAL CASE OUTLINE**



**DATE 29 DEC 2006** 

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- THE NOTION AND TOLETANOING FER ANSI'Y 14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- PHOI HUSION.

  MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION

  SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D

  DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:			
PIN 1.	COLLECTOR	PIN 1.	CATHODE	PIN 1.	COLLECTOR, DYE #1	PIN 1.	COLLECTOR, DYE	#1	
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1		
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2		
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2		
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3		
6.	BASE	6.	NO CONNECTION		BASE, #2	6.	COLLECTOR, #3		
7.	COLLECTOR	7.	ANODE	7.		7.	COLLECTOR, #4		
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4		
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4		
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4		
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3		
12.	EMITTER	12.	CATHODE	12.	COLLECTOR, #3	12.	EMITTER, #3		
13.	BASE	13.	CATHODE	13.	COLLECTOR, #4	13.	BASE, #2	OOL DEDING	COOTDONT
14.	COLLECTOR	14.	NO CONNECTION	14.	BASE, #4	14.	EMITTER, #2	SOLDERING	FOOTPRINT
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1		8X
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1		i.40 — →
								- 0	.40
STYLE 5:		STYLE 6:		STYLE 7:					16X 1.12
PIN 1.	DRAIN, DYE #1		CATHODE	PIN 1.	SOURCE N-CH				10% 1.12
2.	DRAIN, #1		CATHODE	2.	COMMON DRAIN (OUTPU	Τ\		1	16
3.	DRAIN, #2	3.		3.	COMMON DRAIN (OUTPU			<b>, L</b> .	'0
3. 4.	DRAIN, #2	3. 4.	CATHODE	3. 4.	GATE P-CH	1)		<del>-</del> —	
4. 5.	DRAIN, #2	4. 5.	CATHODE	4. 5.	COMMON DRAIN (OUTPU	Τ\		, <b>, , , , , , , , , , , , , , , , , , </b>	
5. 6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU		16	5X 1 -	
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU		0.5	58	, L
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH	•,			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH				
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU	T)			
11.	GATE, #3	11.		11.	COMMON DRAIN (OUTPU				
12.	SOURCE, #3	12.		12.	COMMON DRAIN (OUTPU				
13.	GATE, #2	13.		13.	GATE N-CH	.,			
14.	SOURCE, #2	14.		14.	COMMON DRAIN (OUTPU	T)		<del></del>	V PITCH
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU				1 <u>+=</u> 1- <b>1</b>
16.	SOURCE, #1		ANODE	16.	SOURCE N-CH	.,			
								<b>□</b> 8	9 + - + -
									~ <b></b>
									' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' ' '
									DIMENSIONS: MILLIMETERS

DOCUMENT NUMBER: 98ASB42566B		Electronic versions are uncontrolled except when accessed directly from the Document Repositor, Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-16		PAGE 1 OF 1	

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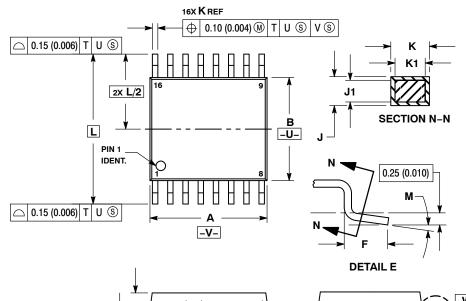
-T- SEATING PLANE





TSSOP-16 CASE 948F-01 ISSUE B

**DATE 19 OCT 2006** 



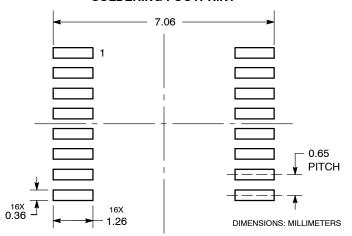
## NOTES

- JIES:
  DIMENSIONING AND TOLERANCING PER
  ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSION A DOES NOT INCLUDE MOLD
  FLASH. PROTRUSIONS OR GATE BURRS.
  MOLD EL ROLL OF GATE BURDS SUAL NO.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
- 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
C		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
7	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
Ы	6.40		0.252	BSC	
М	0 °	8 °	0 °	8 °	

# **SOLDERING FOOTPRINT**

G



# **GENERIC MARKING DIAGRAM\***

168888888 XXXX XXXX **ALYW** 1<del>88888888</del>

XXXX = Specific Device Code Α = Assembly Location

= Wafer Lot L Υ = Year W = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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